Wen-Hsi Lee

List of Publications by Year
in descending order

40	219	1040056 9	1125743 13
papers	citations	h-index	g-index

41	41	41	309
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	First Demonstration of Heterogeneous IGZO/Si CFET Monolithic 3-D Integration With Dual Work Function Gate for Ultralow-Power SRAM and RF Applications. IEEE Transactions on Electron Devices, 2022, 69, 2101-2107.	3.0	9
2	Titanate coupling agent surface modification effect on the magnetic properties of iron-based alloy powder coil prepared using screen printing. Journal of Materials Science: Materials in Electronics, 2021, 32, 1800-1807.	2.2	2
3	Magnetic Properties of Iron-Based Alloy Powder Coils Prepared with Screen Printing Using High-Solid-Content Magnetic Pastes. Journal of Electronic Materials, 2021, 50, 2331-2338.	2.2	2
4	A Novel Method to Fabricate a Thick-Film Cu Electrode Fired in Air Through Printing Al Electrode and Reduction-Oxidation Substitution Reaction. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2021, 11, 485-492.	2.5	3
5	Influence of Plasma Ultraviolet/Vacuum Ultraviolet Irradiation Damage on Silicon Metal-Oxide-Semiconductor Capacitor During Etching. Journal of Nanoscience and Nanotechnology, 2021, 21, 2163-2173.	0.9	0
6	Improvement on Conductivity for Thick Film Aluminum Paste. Journal of Nanoscience and Nanotechnology, 2021, 21, 4726-4734.	0.9	4
7	Improvement on Conductivity for Thick Film Aluminum Paste. Journal of Nanoscience and Nanotechnology, 2021, 21, 4596-4604.	0.9	0
8	A Novel Fabricating a Thick Film Cu-Ni Alloy Resistor by Screen Printing an Al Electrode and Galvanic Replacement Reaction. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2021, 11, 1997-2002.	2.5	2
9	Fabrication of Vertically Stacked Nanosheet Junctionless Field-Effect Transistors and Applications for the CMOS and CFET Inverters. IEEE Transactions on Electron Devices, 2020, 67, 3504-3509.	3.0	29
10	Characteristic of high frequency Fe-Si-Cr material for motor application by selective laser melting. AIP Advances, 2019, 9, .	1.3	14
11	Effect of annealing conditions on dopants activation and stress conservation in silicon-germanium. AIP Advances, 2019, 9, .	1.3	2
12	Neutral beam and ICP etching of HKMG MOS capacitors: Observations and a plasma-induced damage model. Journal of Applied Physics, 2018, 123, 161517.	2.5	3
13	Investigation on Low Firing Copper for Front Electrode of Si-Based Solar Cell Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 2716-2722.	0.9	0
14	Contrasting conduction mechanisms of two internal barrier layer capacitors: (Mn, Nb)-doped SrTiO3 and CaCu3Ti4O12. Journal of Applied Physics, 2017, 121, .	2.5	14
15	A Study on Cu Particles Coated With Nano-Silver by a Replacement Reaction Between Silver Nitrate and Copper Particles. Journal of Nanoscience and Nanotechnology, 2017, 17, 4157-4164.	0.9	4
16	Effect of microwave annealing on electrical characteristics of TiN/Al/TiN/HfO2/Si MOS capacitors. Applied Physics Letters, 2017, 111, .	3.3	12
17	High dopant activation of phosphorus in Ge crystal with high-temperature implantation and two-step microwave annealing. Applied Physics Letters, 2016, 109, .	3.3	6
18	Investigation of high-k/metal gate MOS capacitors annealed by microwave annealing as a post-metal annealing process. , 2016, , .		1

#	Article	IF	Citations
19	Valence and electronic trap states of manganese in SrTiO₃-based colossal permittivity barrier layer capacitors. RSC Advances, 2016, 6, 92127-92133.	3.6	10
20	Activation of high concentrations of phosphorus in germanium by two-steps microwave annealing. , 2016, , .		0
21	A study on the plating and wetting ability of ruthenium-tungsten multi-layers for advanced Cu metallization. , 2016, , .		0
22	Investigation of Barrier Property of Copper Manganese Alloy on Ruthenium. IEEE Transactions on Device and Materials Reliability, 2015, 15, 47-53.	2.0	3
23	A Study on the Diffuse Mechanism and the Barrier Property of Copper Manganese Alloy on Tantalum. IEEE Journal of the Electron Devices Society, 2015, 3, 284-290.	2.1	0
24	Parameter optimization of PT-IGBT breakdown voltage. , 2014, , .		0
25	Optimization of Parameters for TVS breakdown voltage: Design and Fabrication. , 2014, , .		1
26	A Study of Cu/CuMn Barrier for 22-nm Semiconductor Manufacturing. IEEE Transactions on Device and Materials Reliability, 2014, 14, 286-290.	2.0	6
27	A Study of Back Electrode Stacked With Low Cost Reflective Layers For High-Efficiency Thin-Film Silicon Solar Cell. Journal of Solar Energy Engineering, Transactions of the ASME, 2014, 136, .	1.8	2
28	Investigation the Electroplating Behavior of Self Formed CuMn Barrier. Journal of Nanoscience and Nanotechnology, 2013, 13, 5800-5806.	0.9	1
29	Pentacene-Based Thin Film Transistor with Inkjet-Printed Nanocomposite High-K Dielectrics. Active and Passive Electronic Components, 2012, 2012, 1-7.	0.3	5
30	Development of Low Firing NPO Based on (Ca,Sr)(Ti,Zr)O₃for Co-Firing Cu Electrode. Ferroelectrics, 2012, 435, 110-118.	0.6	6
31	USJ formation using solid phase epitaxial regrowth and femtosencond laser anneal. , 2012, , .		0
32	Synthesis of ZnO Nanoparticles to Fabricate a Mask-Free Thin-Film Transistor by Inkjet Printing. Journal of Nanotechnology, 2012, 2012, 1-8.	3.4	11
33	A Study of Trimethylsilane (3MS) and Tetramethylsilane (4MS) Based Î±-SiCN:H/Î±-SiCO:H Diffusion Barrier Films. Materials, 2012, 5, 377-384.	2.9	17
34	Using Chemical-Mechanical Polishing for Planarizing a High-<I>Îº</I> Nanocomposite Polyimide Insulator for Organic Thin Film Transistors Application. Journal of Nanoscience and Nanotechnology, 2011, 11, 1968-1975.	0.9	1
35	Effect of Nanocomposite Gate-Dielectric Properties on Pentacene Microstructure and Field-Effect Transistor Characteristics. Journal of Nanoscience and Nanotechnology, 2010, 10, 762-769.	0.9	6
36	Effect of Under-Layer Treatment of Ta/TaN Barrier Film on Corrosion Between Cu Seed and Ta in Chemical-Mechanical-Polishing Slurry. Journal of Nanoscience and Nanotechnology, 2010, 10, 4196-4203.	0.9	1

#	Article	IF	Citations
37	High performance OTFTs using surface-modified nanocomposite dielectric gate insulator. Journal of Materials Science: Materials in Electronics, 2009, 20, 355-358.	2.2	9
38	Influence of SiO₂ Addition on the Dielectric Properties and Microstructure of (Ba_{0.96}Ca_{0.04})(Ti_{0.85}Zr_{0.15})O₃ Ceramics. International Journal of Applied Ceramic Technology, 2009, 6, 692-701.	2.1	14
39	Study on low temperature sintering and microwave dielectric properties of Ba2Ti9O20-based ceramics. Journal of the Ceramic Society of Japan, 2009, 117, 402-406.	1.1	9
40	Phase development and dielectric properties of BaAl2Si2O8-based low temperature co-fire ceramic material. Journal of the Ceramic Society of Japan, 2008, 116, 935-940.	1.1	10